L Number	Hits	Search Text	DB	Time stamp
164	4	(("4651322") or ("4731792") or ("5870417") or ("5337291")).PN.	USPAT	2003/01/12 13:07
165	1	("5377291").PN.	USPAT	2003/01/12 13:14
166	О	(semiconductor near laser) and faces and cavity and (QW or (quantum near weel)) and (reflection near2 (low or hihg))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/12 13:15
173	193	(semiconductor near laser) and faces and cavity and (QW or (quantum near weLl)) and (reflect\$6 near2 (low or higH))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/12 13:18
180	173	((semiconductor near laser) and faces and cavity and (QW or	DERWENT; IBM_TDB USPAT;	2003/01/12 13:18
		(quantum near weLl)) and (reflect\$6 near2 (low or higH))) AND (active near (medium or region or film or layer))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
187	131	(semiconductor near laser) and faces and cavity and ((active near (medium or region or film or layer)) with (QW or (quantum near weLl))) and (reflect\$6 near2 (low or higH))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/12 13:33
194	54	(semiconductor near laser) and faces and (cavity near3 length) and ((active near (medium or region or film or layer)) with (QW or (quantum near well))) and (reflect\$6 near2 (low or higH))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/12 13:39
201	33	(semiconductor near laser) and faces and (cavity near3 length) and	DERWENT; IBM_TDB USPAT;	2003/01/12 14:19
		((active near (medium or region or film or layer)) with (QW or (quantum near well))) and (reflect\$6 near2 (low\$3)) and (reflect\$6 near2 (hig\$4))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
208	0	2001/0048702	US-PGPUB	2003/01/12 14:19
209	0	Yohida.in.	US-PGPUB	2003/01/12 14:19
210	0	Yohida	US-PGPUB	2003/01/12 14:20
211	1106	Yoshida.in.	US-PGPUB	2003/01/12 14:21
-	768	(semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (mirror or ((low and high) near reflect\$)) and 372/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/12 14:21 2002/06/14 16:26
-	260	((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (mirror or ((low and high) near reflect\$)) and 372/\$) and 372/96	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 18:04
-		(((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (mirror or ((low and high) near reflect\$)) and 372/\$) and 372/96) and (laminat\$ near structure)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/11/29 18:05
	i	(semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and ((low and high) near reflect\$) and 372/\$ and (laminat\$ near structure)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/14 16:28
		((semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near reflect\$) and (laminat\$ near structure)) and 372/\$	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/11/29 18:19

_	5	(semiconductor near laser) and (active near (layer or region or	USPAT;	2001/11/29 19:24
		medium or film) SAME (quantum near well or qw)) and ((low and	US-PGPUB;	2001/11/20 13.24
		high) near reflect\$) and (laminat\$ near structure)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	73	(semiconductor near laser) and (active near (layer or region or	USPAT;	2001/11/29 19:27
		medium or film) SAME (quantum near well or qw)) and ((low and	US-PGPUB;	2001, 11, 20 15.21
		high) near reflect\$)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(semiconductor near laser) and (active near (layer or region or	USPAT:	2001/11/29 19:27
		medium or film) SAME (quantum near well or qw)) and ((low and	US-PGPUB;	2001/11/25 15.27
		high) near mirror) and (laminat\$ near structure)	EPO; JPO;	
		, , , , , , , , , , , , , , , , , , , ,	DERWENT:	
			IBM_TDB	
-	56	((semiconductor near laser) and (active near (layer or region or	USPAT;	2001/11/29 19:28
		medium or film) SAME (quantum near well or qw)) and ((low and	US-PGPUB;	2001/11/29 19:28
		high) near reflect\$)) and 372/\$	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	4	(semiconductor near laser) and (active near (layer or region or	USPAT;	0001/11/00 10 10
		medium or film) SAME (quantum near well or qw)) and ((low and	US-PGPUB;	2001/11/29 19:42
		high) near mirror)	EPO; JPO;	
	İ	B//	DERWENT:	
			IBM_TDB	•
-	1093	(semiconductor near laser) and (active near (layer or region or		0000/00/11 10 00
		medium or film)) and (quantum near well or qw) and (mirror or ((low	USPAT; US-PGPUB;	2002/06/14 16:36
		and high) near reflect\$)) and substrate	EPO; JPO;	
		and mgm/ near refrection// and substrate	DERWENT;	
			IBM_TDB	
_	186	(semiconductor near laser) and (active near (layer or region or	USPAT;	0000/00/14 10 10
		medium or film)) and (quantum near well or qw) and (low near	US-PGPUB;	2002/06/14 16:48
		reflect\$5)and (high near reflect\$5) and substrate	EPO; JPO;	
		and substrate	DERWENT;	
			1	
_	113	((semiconductor near laser) and (active near (layer or region or	IBM_TDB	0000/00/11 17 77
		medium or film)) and (quantum near well or qw) and (low near	USPAT;	2002/06/14 17:25
		reflect\$5)and (high near reflect\$5) and substrate) and cavity	US-PGPUB;	
		refrectional (fight feat refrection) and substrate) and cavity	EPO; JPO;	
			DERWENT;	
_	63	((semiconductor near laser) and (active near (layer or region or	IBM_TDB	2002/22/11 17 22
		medium or film)) and (quantum near well or qw) and (low near	USPAT;	2002/06/14 17:26
		reflect\$5)and (high near reflect\$5) and substrate) and (cavity near2	US-PGPUB;	
		length)	EPO; JPO;	
		b/	DERWENT;	
_	43	((semiconductor near laser) with (optical near fiber)) and (active near	IBM_TDB	0000/00/10 11
	10	(layer or region or medium or film)) and (quantum near well or qw)	USPAT;	2002/06/16 15:26
		and ((low and high) near reflect\$) and substrate	US-PGPUB;	
		ma (1000 and mgn) near renector and substrate	EPO; JPO;	
			DERWENT;	
			IBM_TDB	